

Vishay Siliconix

## Single 4:1 Low r<sub>ON</sub> Multiplexers

#### DESCRIPTION

The DG2034 is a low voltage, low  $r_{ON}$ , high bandwidth single 4 to 1 analog multiplexer designed for high performance switching of analog and video signals. Combining low power; fast switching; low on-resistance, flatness and matching; and small physical size, the DG2034 is ideal for portable and battery applications.

Built on Vishay Siliconix's low voltage CMOS process, the DG2034 has an epitaxial layer which prevents latchup. Break-before-make is guaranteed.

### FEATURES

- Low voltage operation (1.8 V to 5.5 V)
- Low on-resistance r<sub>DS(on)</sub>: 4 Ω
- Off-isolation and crosstalk: 55 dB at 10 MHz
- Fast switch 25 ns t<sub>ON</sub>
- Low charge injection Q<sub>INJ</sub>: 4.7 pC
- Low power consumption 4 μW

#### BENEFITS

- High accuracy
- High bandwidth
- TTL and low voltage logic compatibility
- Low power consumption
- Reduced PCB space

#### **APPLICATIONS**

- · Mixed signal routing
- · Portable and battery operated systems
- · Low voltage data acquisition
- Modems
- PCMCIA cards

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Top view								
TRUTH TABLE								
A1	A0	EN	ON Switch					
Х	Х	0	None					
0	0	1	S1					
0	1	1	S2					
1	0	1	S3					
1	1	1	S4					



ORDERING INFORMATION						
Temp Range Package Part Number						
- 40 °C to 85 °C	MSOP-10	DG2034DQ-T1-E3				
	12-pin QFN (3 x 3 mm)	DG2034DN-T1-E4				



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ABSOLUTE MAXIMUM RA	TINGS			
Parameter		Limit	Unit	
Referenced V+ to GND	- 0.3 to + 6			
A <sub>X</sub> , E <sub>N</sub> , S <sub>X</sub> , COM <sup>a</sup>		- 0.3 to (V+ + 0.3)	V	
Continuous Current (Any Terminal)		± 50		
Peak Current (Pulsed at 1 ms, 10 % du	ity cycle)	± 100	— mA	
	QFN-12 (3 x 3 mm) <sup>c</sup>	1295	mW	
Power Dissipation (Packags) <sup>b</sup>	MSOP-10 <sup>d</sup>	320	11100	
Storage Temperature (D Suffix)	·	- 65 to 150		

#### Notes:

a. Signals on S<sub>X</sub>, D<sub>X</sub>, EN or A<sub>X</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board.
c. Derate 16.2 mV/°C above 70 °C.
d. Derate 4.0 mV/°C above 70 °C.

SPECIFICATIONS (V+	= 3 V)							
		Test Conditions Otherwise Unless Speci	Conditions Unless Specified				°C	
Parameter	Symbol	V+ = 3 V, ± 10 %, V <sub>AL</sub> = 0.4 V, V <sub>AH</sub> = 1.5 V <sup>e</sup>		Temp. <sup>a</sup>	Min. <sup>c</sup>	Typ. <sup>b</sup>	Max. <sup>c</sup>	Unit
Analog Switch	-						-	
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>		Full	0		V+	V	
On-Resistance	r <sub>ON</sub>		Room Full		4	7 9		
r <sub>ON</sub> Match	$\Delta r_{ON}$	$V_{+} = 2.7 V, V_{COM} = 0.5 V/1.5$ $I_{S} = 10 mA$	V/2.0 V	Room		0.1	0.3	Ω
r <sub>ON</sub> Flatness <sup>d,f</sup>	r <sub>ON</sub> Flatness		Room		0.3	1.5		
Off Leakage Current <sup>g</sup>	I <sub>S(off)</sub>	V+ = 3.3 V, V <sub>S</sub> = 1 V/3 V V <sub>COM</sub> = 3 V/1 V, V <sub>EN</sub> = 0 V		Room Full	- 1 - 10	0.3	1 10	nA
COM Off Leakage Current <sup>g</sup>	I <sub>COM(off)</sub>			Room Full	- 1 - 10	0.3	1 10	
Channel-On Leakage Current <sup>g</sup>	I <sub>COM(on)</sub>	V+ = 3.3 V V <sub>COM</sub> = V <sub>S</sub> = 1 V/3 V	Room Full	- 1 - 10	0.3	1 10		
Digital Control								
Input Current <sup>d</sup>	I <sub>A</sub> or I <sub>EN</sub>	V <sub>A/EN</sub> = 0 or V+, See Truth	Full	- 1.0		1.0	μΑ	
Input High Voltage <sup>d</sup>	$V_{\text{AH}}  \text{or}  V_{\text{ENH}}$							v
Input Low Voltage <sup>d</sup>	$V_{AL}  \text{or}  V_{ENL}$		Full			0.4	v	
Dynamic Characteristics	-						-	-
Turn-On Time	t <sub>ON</sub>			Room Full		25	35 45	
Turn-Off Time	t <sub>OFF</sub>	$V_{\rm S}$ = 1.5 V, R <sub>L</sub> = 300 G	2	Room Full		15	25 35	ns
Break-Before-Make Time <sup>d</sup>	t <sub>D</sub>			Room		10.5		
Transition Time	t <sub>trans</sub>	$\rm V_S$ = 1.5 V/0 V, $\rm V_S$ = 0 V/1.5 V, $\rm R_L$ = 300 $\Omega$		Room Full		30	45 55	
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L = 1 \text{ nF}, V_{gen} = 0 \text{ V}, \text{ R}_{gen}$	= 0 Ω	Room		- 4.7		рС
Off-Isolation <sup>d</sup>	OIRR	$R_{L} = 50 \Omega, C_{L} = 5 pF$ $f = 1 MHz$		Room		- 73		
Oll-Isolalion	0		f = 10 MHz	Room		- 54		dB
Channel-to-Channel Crosstalk <sup>d</sup>	X <sub>TALK</sub>	$R_L = 50 $ Ω, $C_L = 5 $ pF	f = 1 MHz f = 10 MHz	Room Room		- 77 - 59		
Off Capacitance <sup>d</sup>	C <sub>S(off)</sub>	V+ = 2.7 V, f = 1 MHz		Room		14		
COM Off Capacitance <sup>d</sup>	C <sub>COM(off)</sub>			Room		46		pF
COM On Capacitance <sup>d</sup>	C <sub>COM(on)</sub>			Room		67		
Power Supply						•		
Power Supply Range	V+				2.7		3.3	V
Power Supply Current <sup>d</sup>	l+	V+ = 3.3 V, $V_{A/EN}$ = 0 or 3.3 V, See	Full			1.0	μA	



		Test Conditions Otherwise Unless Specif	fied		Limits - 40 to 85 °C			
Parameter	<b>Symbol</b> $V_{+} = 3 V_{+} \pm 10 \%, V_{AL} = 0.8 V \text{ or } V_{AH} = 2.4 V^{e}$				Min. <sup>c</sup>	Typ. <sup>b</sup>	Max. <sup>c</sup>	Unit
Analog Switch								
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>			Full	0		V+	V
On-Resistance	r <sub>ON</sub>		Room Full		3	5.5 7		
r <sub>ON</sub> Match	$\Delta r_{ON}$	V+ = 4.5 V, V <sub>COM</sub> = 1.5 V/2.5 <sup>v</sup> I <sub>S</sub> = 10 mA	V/3.5 V	Room		0.16	0.5	Ω
r <sub>ON</sub> Flatness <sup>d,f</sup>	r <sub>ON</sub> Flatness	·S = 10 m/c		Room		0.6	1.5	
Off Leakage Current	I <sub>S(off)</sub>	V+ = 5.5 V, V <sub>S</sub> = 1 V/4.5 V V <sub>COM</sub> = 4.5 V/1 V, V <sub>EN</sub> = 0 V		Room Full	- 1 - 10	0.5	1 10	
COM Off Leakage Current	I <sub>COM(off)</sub>			Room Full	- 1 - 10	0.5	1 10	nA
Channel-On Leakage Current	I <sub>COM(on)</sub>	V+ = 5.5 V, V <sub>COM</sub> = V <sub>S</sub> = 1 V	Room Full	- 1 - 10	0.5	1 10		
Digital Control								
Input Current <sup>d</sup>	$I_{AH}$ or $I_{ENH}$	V <sub>A</sub> or V <sub>EN</sub> = 0 or V+, See Trut	Full	- 1.0		1.0	μA	
Input High Voltage <sup>d</sup>	$V_{\text{AH}}  \text{or}  V_{\text{ENH}}$			Full	2.4			v
Input Low Voltage <sup>d</sup>	$V_{\text{AL}}  \text{or}  V_{\text{ENL}}$		Full			0.8	v	
Dynamic Characteristics						-		-
Turn-On Time	t <sub>ON</sub>			Room Full		18	30 40	ns
Turn-Off Time	t <sub>OFF</sub>	$V_{S}$ = 3.0 V, $R_{L}$ = 300 $\Omega$	1	Room Full		12	20 30	
Break-Before-Make Time <sup>d</sup>	t <sub>D</sub>			Room		10.5		
Transition Time	t <sub>trans</sub>	$V_{S}$ = 3 V/0 V, $V_{S}$ = 0 V/3 V, $R_{L}$	= 300 Ω	Room Full		25	40 50	
Off-Isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega, C_1 = 5 p$ f = 1 MHz		Room		- 73		
		$R_{L} = 50 \ \Omega, C_{L} = 5 \ pF \qquad \qquad \frac{f = 10 \ MHz}{f = 10 \ MHz}$		Room		- 53.5		dB
Channel-to-Channel Crosstalk <sup>d</sup>	X <sub>TALK</sub>			Room Room		- 77 - 60.2		
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L = 1 \text{ nF}, V_{gen} = 0 \text{ V}, \text{ R}_{gen} = 0 \Omega$		Room		- 4.4		Dq
Off Capacitance <sup>d</sup>	C <sub>S(off)</sub>	gen - yen		Room		13		P 0
COM Off Capacitance <sup>d</sup>	C <sub>COM(off)</sub>	V+ = 5 V, f = 1 MHz		Room		43		pF
COM On Capacitance <sup>d</sup>	C <sub>COM(on)</sub>			Room		64		
Power Supply	SCOW(off)			nooni		0.1		
Power Supply Range	V+				4.5		5.5	V
Power Supply Current	l+	V+ = 5.5 V, V <sub>A/EN</sub> = 0 or 5.5 V, See	Full	-		1.0	μA	

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, not subjected to production test.

e.  $V_A$ ,  $E_N$  = input voltage to perform proper function.

f. Difference of min and max values.

g. Guaranteed by 5 V testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





### DG2034 Vishay Siliconix

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



### DG2034

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### **TEST CIRCUITS**





Note: Logic input waveform is inverted for switches that have the opposite logic sense control





C<sub>L</sub> (includes fixture and stray capacitance)











#### **TEST CIRCUITS**





IN dependent on switch configuration Input polarity determined by sense of switch.

Figure 4. Charge Injection



Figure 6. Off Isolation

Figure 7. Source/Drain Capacitances

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72418.



### Package Information Vishay Siliconix

#### MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)







#### NOTES:

/4.\

/5.\

1. Die thickness allowable is  $0.203 \pm 0.0127$ .

2. Dimensioning and tolerances per ANSI.Y14.5M-1994.

/3. Dimensions "D" and "E<sub>1</sub>" do not include mold flash or protrusions, and are measured at Datum plane \_-H- , mold flash or protrusions shall not exceed 0.15 mm per side.

Dimension is the length of terminal for soldering to a substrate.

Terminal positions are shown for reference only.

6. Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.

The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".

/8. Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

9. Controlling dimension: millimeters.

10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

11 Datums -A- and -B- to be determined Datum plane -H-.

12 Exposed pad area in bottom side is the same as teh leadframe pad size.











N = 10L

	М	MILLIMETERS				
Dim	Min	Nom	Max	Note		
Α	-	-	1.10			
A <sub>1</sub>	0.05	0.10	0.15			
A <sub>2</sub>	0.75	0.85	0.95			
b	0.17	-	0.27	8		
b <sub>1</sub>	0.17	0.20	0.23	8		
С	0.13	-	0.23			
<b>c</b> <sub>1</sub>	0.13	0.15	0.18			
D		3				
Е		4.90 BSC				
E <sub>1</sub>	2.90	3.00	3.10	3		
е		0.50 BSC				
е <sub>1</sub>		2.00 BSC				
L	0.40	0.55	0.70	4		
Ν		5				
x	0°	4°	6°			
CN: T-02 DWG: 58	2080—Rev. 0 67	C, 15-Jul-02				



### **Package Information** Vishay Siliconix

### **QFN-12 LEAD (3 X 3)**





		MILLIMETERS			INCHES					
	Dim	Min	Nom	Max	Min	Nom	Max			
	Α	0.80	0.90	1.00	0.032	0.035	0.039			
ns are in millimeters.	b	0.18	0.23	0.30	0.007	0.009	0.012			
number of terminals.	D	3.00 BSC			0.118 BSC					
applies to metallized terminal and is measured	D2	1.00	1.15	1.25	0.039	0.045	0.049			
5 and 0.30 mm from terminal tip.	E		3.00 BSC			0.118 BSC				
applies to the exposed heat sink slug as well as the	E2	1.00	1.15	1.25	0.039	0.045	0.049			
	е	0.50 BSC			0.02 BSC					
lentifier may be either a mold or marked feature, it ted within the zone iindicated.	L	0.45	0.55	0.65	0.018	0.022	0.026			
	AA	0.435			0.017					
	BB		0.435			0.017				
	CC		0.18			0.007				
	DD		0.18			0.007				

ECN: C-03092—Rev. A, 14-Apr-03 DWG: 5898

NOTES:

- 1. All dimensions
- 2. N is the total n



Dimension b a between 0.25

- <u>/4</u>. Coplanarity ap terminal.
- 5. The pin #1 ide must be locate



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